

AMENDMENTS TO THE CLAIMS:

1. 1. (Previously Presented) A thin film transistor including:
 2. a back channel electrode,
 3. wherein a voltage of a front channel positioned on the side of a gate wiring of said thin film transistor is made equal to a voltage of said back channel positioned on the side of a back channel electrode by short-circuiting said back channel electrode to a gate electrode through a contact-hole provided in a portion of semiconductor layer forming said thin film transistor.
2. (Original) A thin film transistor as claimed in claim 1, wherein said back channel electrode is formed of the same material as a material of a pixel electrode connected to one of source and drain electrodes of said thin film transistor.
3. (Original) A thin film transistor as claimed in claim 2, wherein said pixel electrode is a transparent electrode.
4. 4. (Previously Presented) A thin film transistor including:
 2. a back channel electrode,
 3. wherein a voltage of a front channel positioned on the side of a gate wiring of said thin film transistor is made equal to a voltage of said back channel positioned on the side of a back channel electrode by short-circuiting said back channel electrode to a gate electrode through a contact-hole provided in a portion of a semiconductor layer forming said thin film transistor, and
 8. wherein said contact-hole is formed in a location remote from an active region of said thin film transistor by at least five microns.
5. 5. (Previously Presented) A thin film transistor including:
 2. a back channel electrode,
 3. wherein a voltage of a front channel positioned on the side of a gate wiring of said thin film transistor is made equal to a voltage of said back channel positioned on the side of a

5 back channel electrode by short-circuiting said back channel electrode to a gate electrode
6 through a contact-hole provided in a portion of a semiconductor layer forming said thin film
7 transistor, and

8 wherein a passivation film patterned to have a width equal to that of said back channel
9 electrode and said semiconductor layer are provided between said back channel and a gate
10 insulating film.

1 6. (Currently Amended) A thin film transistor ~~as claimed in claim 1 including:~~
2 a back channel electrode,
3 wherein a voltage of a front channel positioned on the side of a gate wiring of said
4 thin film transistor is made equal to a voltage of said back channel positioned on the side of a
5 back channel electrode by short-circuiting said back channel electrode to a gate electrode
6 through a contact-hole provided in a portion of semiconductor layer forming said thin film
7 transistor, and

8 wherein said semiconductor layer patterned to have a width equal to that of source and
9 drain electrodes of said thin film transistor is provided between said source and drain
10 electrodes and a gate insulating film.

7. (Previously Presented) A thin film transistor as claimed in claim 1, wherein said
semiconductor layer has an ohmic contact layer on the side thereof, which is in contact with
source and drain electrodes.

8-12. (Canceled)

1 13. (Previously Presented) A thin film transistor including a back channel electrode,
2 wherein a voltage of a front channel positioned on the side of a gate wiring of said thin film
3 transistor is made equal to a voltage of said back channel positioned on the side of a back
4 channel electrode by short-circuiting said back channel electrode to a gate electrode through a
5 contact-hole provided in a portion of a layer forming said thin film transistor, and

6 wherein said contact-hole is formed in a location remote from an active region of said
7 thin film transistor by at least five microns.

1 14. (Previously Presented) A thin film transistor including a back channel electrode,
2 wherein a voltage of a front channel positioned on the side of a gate wiring of said thin film
3 transistor is made equal to a voltage of said back channel positioned on the side of a back
4 channel electrode by short-circuiting said back channel electrode to a gate electrode through a
5 contact-hole provided in a portion of a layer forming said thin film transistor, and

6 wherein a passivation film patterned to have a width equal to that of said back channel
7 electrode and said layer are provided between said back channel and a gate insulating film of
8 said film transistor.

1 15. (Previously Presented) A thin film transistor including:

2 a back channel electrode,

3 wherein a voltage of a front channel positioned on the side of a gate wiring of said
4 thin film transistor is made equal to a voltage of said back channel positioned on the side of a
5 back channel electrode by short-circuiting said back channel electrode to a gate electrode
6 through a contact-hole provided in a portion of a semiconductor layer forming said thin film
7 transistor, and

8 wherein said layer patterned to have a width equal to that of source and drain
9 electrodes of said thin film transistor is provided between said source and drain electrodes
10 and a gate insulating film of said film transistor.

1 16. (Previously Presented) A thin film transistor including:

2 a back channel electrode,

3 wherein a voltage of a front channel positioned on the side of a gate wiring of said
4 thin film transistor is made equal to a voltage of said back channel positioned on the side of a
5 back channel electrode by short-circuiting said back channel electrode to a gate electrode
6 through a contact-hole provided in a portion of a semiconductor layer forming said thin film
7 transistor, and

8 wherein said layer has an ohmic contact layer on the side thereof, which is in contact
9 with source and drain electrodes of said film transistor.

17-23. (Canceled)

24. (New) A thin film transistor as claimed in claim 1, wherein said portion of said semiconductor layer forming said thin film transistor contact-hole for short-circuiting said back gate electrode ands said gate electrode comprises an active layer.

25. (New) A thin film transistor as claimed in claim 16, wherein said portion of said semiconductor layer forming said thin film transistor contact-hole for short-circuiting said back gate electrode ands said gate electrode comprises an active layer.